September 2013



## FNC42060F / FNC42060F2

## Motion SPM® 45 Series

### **Features**

- UL Certified No. E209204
- 600 V, 20 A 3 Phase IGBT Inverter Including Control ICs for Gate Drive and Protections
- Easy PCB Layout Thanks to The Built In Bootstrap Diodes and The Dedicated Vs Pins
- Three Separate Open Emitter Pins from Low Side IGBTs for Three Leg Current Sensing
- Single Grounded Power Supply with Bootstrap Operations
- Built In NTC Thermistor for Over Temperature Monitoring
- · Isolation Rating of 2000 Vrms / min.

## **Applications**

· Motion Control - Home Appliance / Industrial Motor

### **Related Resources**

- AN 9070 : Motion SPM® 45 Series Users Guide
- AN 9071: Motion SPM® 45 Series Thermal Performance Information
- AN 9072: Motion SPM® 45 Series Mounting Guidance
- RD 344 : Reference Design (Three Shunt Solution)
- RD 345 : Reference Design (One Shunt Solution)

## **General Description**

FNC42060F / FNC42060F2 Is A Motion SPM<sup>®</sup> 45 Series that Fairchild Has Newly Developed to Provide A Very Compact and High Performance Inverter Solution for AC Motor Drives in Low - Power Applications Such as Air Conditioners and Refrigerators. It Combines Low - Loss Short - Circuit Rated IGBTs and Optimized Gate Drivers in A Fully Isolated Package to Deliver A Simple and Robust Design. The System Reliability Is Further Enhanced by The Built - In NTC for Temperature Monitoring, Integrated Under - Voltage Lock - Out Function for Both High and Low Side, and An Over - Current Protection Input. Three Separate Open - Emitter Pins for Low Side IGBTs Make Three Leg Current Sensing Possible. Built - In Bootstrap Diodes and Dedicated VS Pins Make PCB Layout Easy.



Figure 1. Package Overview

## **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Packing Type	Reel Size	Tape Width	Quantity
FNC42060F	FNC42060F	SPMAA - A26	RAIL	-	-	12
FNC42060F2	FNC42060F2	SPMAA - C26	RAIL	-	-	12

## **Integrated Power Functions**

• 600 V - 20 A IGBT inverter for three - phase DC / AC power conversion (Please refer to Figure 3)

## Integrated Drive, Protection and System Control Functions

- For inverter high side IGBTs: Gate drive circuit, High voltage isolated high speed level shifting Control circuit under - voltage (UV) protection
- For inverter low side IGBTs: Gate drive circuit, Short circuit protection (SC)
   Control supply circuit under voltage (UV) protection
- Fault signaling: Corresponding to UV (low side supply) and SC faults
- Input interface: Active high interface, schmitt trigger input, can work with 3.3 / 5 V logic

## **Pin Configuration**

## **Top View**

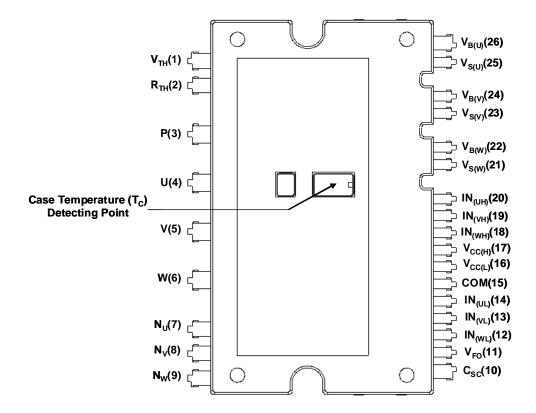
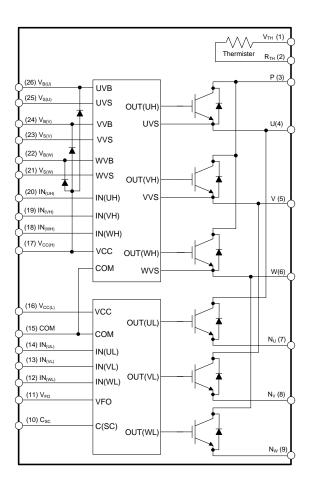


Figure 2.

# **Pin Descriptions**

Pin Number	Pin Name	Pin Description
1	V <sub>TH</sub>	Thermistor Bias Voltage
2	R <sub>TH</sub>	Series Resistor for the Use of Thermistor (Temperature Detection)
3	Р	Positive DC - Link Input
4	U	Output for U Phase
5	V	Output for V Phase
6	W	Output for W Phase
7	N <sub>U</sub>	Negative DC - Link Input for U Phase
8	N <sub>V</sub>	Negative DC - Link Input for V Phase
9	N <sub>W</sub>	Negative DC - Link Input for W Phase
10	C <sub>SC</sub>	Capacitor (Low - Pass Filter) for Short - Current Detection Input
11	V <sub>FO</sub>	Fault Output
12	IN <sub>(WL)</sub>	Signal Input for Low - Side W Phase
13	IN <sub>(VL)</sub>	Signal Input for Low - Side V Phase
14	IN <sub>(UL)</sub>	Signal Input for Low - Side U Phase
15	СОМ	Common Supply Ground
16	V <sub>CC(L)</sub>	Low - Side Common Bias Voltage for IC and IGBTs Driving
17	V <sub>CC(H)</sub>	High - Side Common Bias Voltage for IC and IGBTs Driving
18	IN <sub>(WH)</sub>	Signal Input for High - Side W Phase
19	IN <sub>(VH)</sub>	Signal Input for High - Side V Phase
20	IN <sub>(UH)</sub>	Signal Input for High - Side U Phase
21	V <sub>S(W)</sub>	High - Side Bias Voltage Ground for W Phase IGBT Driving
22	V <sub>B(W)</sub>	High - Side Bias Voltage for W Phase IGBT Driving
23	V <sub>S(V)</sub>	High - Side Bias Voltage Ground for V Phase IGBT Driving
24	V <sub>B(V)</sub>	High - Side Bias Voltage for V Phase IGBT Driving
25	V <sub>S(U)</sub>	High - Side Bias Voltage Ground for U Phase IGBT Driving
26	V <sub>B(U)</sub>	High - Side Bias Voltage for U Phase IGBT Driving

## **Internal Equivalent Circuit and Input/Output Pins**



#### Note

- 1) Inverter high side is composed of three IGBTs, freewheeling diodes and one control IC for each IGBT.
- 2) Inverter low side is composed of three IGBTs, freewheeling diodes and one control IC for each IGBT. It has gate drive and protection functions.
- 3) Inverter power side is composed of four inverter dc link input terminals and three inverter output terminals.

Figure 3.

## **Absolute Maximum Ratings** (T<sub>J</sub> = 25°C, Unless Otherwise Specified)

## **Inverter Part**

Symbol	Parameter	Conditions	Rating	Unit
$V_{PN}$	Supply Voltage	Applied between P - N <sub>U</sub> , N <sub>V</sub> , N <sub>W</sub>	450	V
V <sub>PN(Surge)</sub>	Supply Voltage (Surge)	Applied between P - N <sub>U</sub> , N <sub>V</sub> , N <sub>W</sub>	500	V
V <sub>CES</sub>	Collector - Emitter Voltage		600	V
± I <sub>C</sub>	Each IGBT Collector Current	$T_C = 25^{\circ}C, T_J < 150^{\circ}C$	20	Α
± I <sub>CP</sub>	Each IGBT Collector Current (Peak)	$T_{C}$ = 25°C, $T_{J}$ < 150°C, Under 1 ms Pulse Width	40	А
P <sub>C</sub>	Collector Dissipation	T <sub>C</sub> = 25°C per One Chip	50	W
T <sub>J</sub>	Operating Junction Temperature	(Note 1)	- 40 ~ 150	°C

#### Note:

### **Control Part**

Symbol	Parameter	Conditions	Rating	Unit
V <sub>CC</sub>	Control Supply Voltage	Applied between $V_{CC(H)}$ , $V_{CC(L)}$ - COM	20	V
V <sub>BS</sub>	High - Side Control Bias Voltage	$ \begin{array}{c} \text{Applied between $V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$,} \\ V_{B(W)} \text{ - $V_{S(W)}$} \end{array} $	20	V
V <sub>IN</sub>	Input Signal Voltage	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	- 0.3 ~ V <sub>CC</sub> + 0.3	V
V <sub>FO</sub>	Fault Output Supply Voltage	Applied between V <sub>FO</sub> - COM	- 0.3 ~ V <sub>CC</sub> + 0.3	V
I <sub>FO</sub>	Fault Output Current	Sink Current at V <sub>FO</sub> pin	1	mA
V <sub>SC</sub>	Current Sensing Input Voltage	Applied between C <sub>SC</sub> - COM	- 0.3 ~ V <sub>CC</sub> + 0.3	٧

## **Bootstrap Diode Part**

Symbol	Parameter	Conditions	Rating	Unit
V <sub>RRM</sub>	Maximum Repetitive Reverse Voltage		600	V
I <sub>F</sub>	Forward Current	$T_{C} = 25^{\circ}C, T_{J} < 150^{\circ}C$	0.50	Α
I <sub>FP</sub>	Forward Current (Peak)	$T_{C}$ = 25°C, $T_{J}$ < 150°C, Under 1 ms Pulse Width	1.50	Α
TJ	Operating Junction Temperature		- 40 ~ 150	°C

## **Total System**

Symbol	Parameter	Conditions	Rating	Unit
V <sub>PN(PROT)</sub>	Self Protection Supply Voltage Limit (Short Circuit Protection Capability)	$V_{CC} = V_{BS} = 13.5 \sim 16.5 \text{ V}$ T <sub>J</sub> = 150°C, Non - repetitive, less than 2 μs	400	V
T <sub>STG</sub>	Storage Temperature		- 40 ~ 125	°C
V <sub>ISO</sub>	Isolation Voltage	60 Hz, Sinusoidal, AC 1 minute, Connection pins to heat sink plate	2000	V <sub>rms</sub>

### **Thermal Resistance**

Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
R <sub>th(j-c)Q</sub>	Junction to Case Thermal Resistance	Inverter IGBT part (per 1 / 6 module)	-	-	2.50	°C/W
R <sub>th(j-c)F</sub>		Inverter FWD part (per 1 / 6 module)	-	-	3.60	°C/W

#### Note:

<sup>1.</sup> The maximum junction temperature rating of the power chips integrated within the Motion SPM $^8$  45 product is 150°C.

<sup>2.</sup> For the measurement point of case temperature ( $T_{\mbox{\scriptsize C}}$ ), please refer to Figure 2.

## **Electrical Characteristics** (T<sub>J</sub> = 25°C, Unless Otherwise Specified)

### **Inverter Part**

S	ymbol	Parameter	Cond	itions	Min.	Тур.	Max.	Unit
V	CE(SAT)	Collector - Emitter Saturation Voltage	$V_{CC} = V_{BS} = 15 \text{ V}$ $V_{IN} = 5 \text{ V}$	I <sub>C</sub> = 20 A, T <sub>J</sub> = 25°C	-	1.85	2.35	V
	V <sub>F</sub>	FWD Forward Voltage	V <sub>IN</sub> = 0 V	I <sub>F</sub> = 20 A, T <sub>J</sub> = 25°C	-	1.95	2.45	V
HS	t <sub>ON</sub>	Switching Times	$V_{PN} = 300 \text{ V}, V_{CC} = V_{BS} = 15 \text{ V}, I_{C} = 20 \text{ A}$		0.45	0.75	1.25	μS
	t <sub>C(ON)</sub>		$T_J = 25^{\circ}C$ $V_{} = 0 V \leftrightarrow 5 V Induce$	tive load	-	0.20	0.45	μS
	t <sub>OFF</sub>		$V_{IN} = 0 \text{ V} \leftrightarrow 5 \text{ V}$ , Inductive load (Note 3)		-	0.70	1.20	μS
	t <sub>C(OFF)</sub>				-	0.15	0.40	μS
	t <sub>rr</sub>				-	0.15	-	μS
LS	t <sub>ON</sub>		$V_{PN} = 300 \text{ V}, V_{CC} = V_{E}$	<sub>3S</sub> = 15 V, I <sub>C</sub> = 20 A	0.45	0.75	1.25	μS
	t <sub>C(ON)</sub>		$T_J = 25^{\circ}C$ $V_{IN} = 0 V \leftrightarrow 5 V$ , Induc	tive load	-	0.20	0.45	μS
	t <sub>OFF</sub>		(Note 3)	aive load	-	0.75	1.25	μS
	t <sub>C(OFF)</sub>				-	0.15	0.40	μS
	t <sub>rr</sub>				-	0.15	-	μS
	I <sub>CES</sub>	Collector - Emitter Leakage Current	V <sub>CE</sub> = V <sub>CES</sub>		-	-	5	mA

#### Note

<sup>3.</sup>  $t_{ON}$  and  $t_{OFF}$  include the propagation delay time of the internal drive IC.  $t_{C(ON)}$  and  $t_{C(OFF)}$  are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

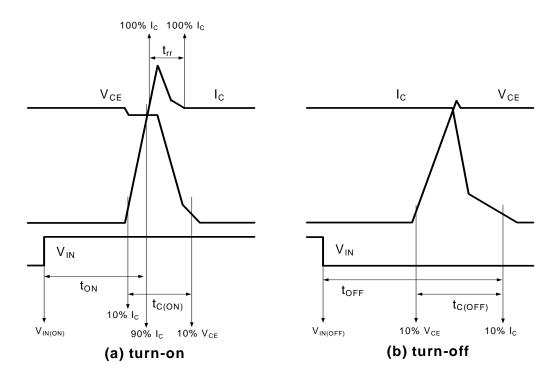


Figure 4. Switching Time Definition

## **Switching Loss (Typical)**

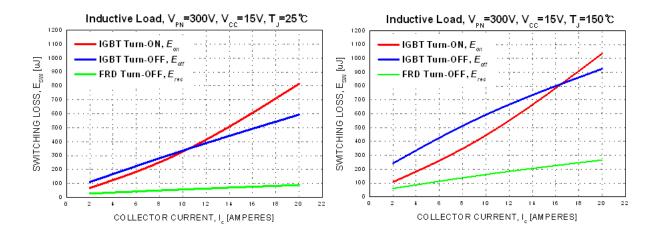


Figure 5. Switching Loss Characteristics

### **Control Part**

Symbol	Parameter	Conditions	}	Min.	Тур.	Max.	Unit
I <sub>QCCH</sub>	Quiescent V <sub>CC</sub> Supply	V <sub>CC(H)</sub> = 15 V, IN <sub>(UH,VH,WH)</sub> = 0 V	V <sub>CC(H)</sub> - COM	-	-	0.10	mA
I <sub>QCCL</sub>	Current	V <sub>CC(L)</sub> = 15 V, IN <sub>(UL,VL, WL)</sub> = 0 V	V <sub>CC(L)</sub> - COM	-	-	2.65	mA
І <sub>РССН</sub>	Operating V <sub>CC</sub> Supply Current	$V_{CC(H)}$ = 15 V, $f_{PWM}$ = 20 kHz, duty = 50%, applied to one PWM signal input for high - side	V <sub>CC(H)</sub> - COM	-	-	0.15	mA
I <sub>PCCL</sub>		$V_{CC(L)}$ = 15 V, $f_{PWM}$ = 20 kHz, duty = 50%, applied to one PWM signal input for low - side	V <sub>CC(L)</sub> - COM	-	-	4.00	mA
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> Supply Current	V <sub>BS</sub> = 15 V, IN <sub>(UH, VH, WH)</sub> = 0 V	$V_{B(U)} - V_{S(U)}, V_{B(V)} - V_{S(V)}, V_{B(W)} - V_{S(W)}$	-	-	0.30	mA
I <sub>PBS</sub>	Operating V <sub>BS</sub> Supply Current	V <sub>CC</sub> = V <sub>BS</sub> = 15 V, f <sub>PWM</sub> = 20 kHz, duty = 50%, applied to one PWM signal input for high - side		-	-	2.00	mA
V <sub>FOH</sub>	Fault Output Voltage	$V_{SC} = 0 \text{ V}, V_{FO} \text{ Circuit: } 10 \text{ k}\Omega \text{ to 5 } V_{SC}$	$V_{SC} = 0 \text{ V}, V_{FO} \text{ Circuit: } 10 \text{ k}\Omega \text{ to 5 V Pull - up}$		-	-	V
V <sub>FOL</sub>		$V_{SC} = 1 \text{ V}, V_{FO} \text{ Circuit: } 10 \text{ k}\Omega \text{ to } 5 \text{ V}$	/ Pull - up	-	-	0.5	V
V <sub>SC(ref)</sub>	Short Circuit Trip Level	V <sub>CC</sub> = 15 V (Note 4)		0.45	0.5	0.55	V
UV <sub>CCD</sub>		Detection level		10.5	-	13.0	V
UV <sub>CCR</sub>	Supply Circuit Under - Voltage	Reset level		11.0	-	13.5	V
UV <sub>BSD</sub>	Protection	Detection level		10.0	-	12.5	V
UV <sub>BSR</sub>		Reset level		10.5	-	13.0	V
t <sub>FOD</sub>	Fault - Out Pulse Width			30	-	-	μS
V <sub>IN(ON)</sub>	ON Threshold Voltage	Applied between $IN_{(UH)}$ , $IN_{(VH)}$ , $IN_{(WH)}$ , $IN_{(UL)}$ , $IN_{(VL)}$ , $IN_{(WL)}$ - COM		-	-	2.6	V
V <sub>IN(OFF)</sub>	OFF Threshold Voltage			0.8	-	-	V
R <sub>TH</sub>	Resistance of	@T <sub>TH</sub> = 25°C, (Note 5)	@T <sub>TH</sub> = 25°C, (Note 5)		47	-	kΩ
	Thermister	@T <sub>TH</sub> = 100°C		-	2.9	-	kΩ

#### Note:

<sup>4.</sup> Short - circuit current protection is functioning only at the low - sides.

 $<sup>5.\</sup> T_{TH}\ is\ the\ temperature\ of\ thermister\ itselt.\ To\ know\ case\ temperature\ (T_C),\ please\ make\ the\ experiment\ considering\ your\ application.$ 

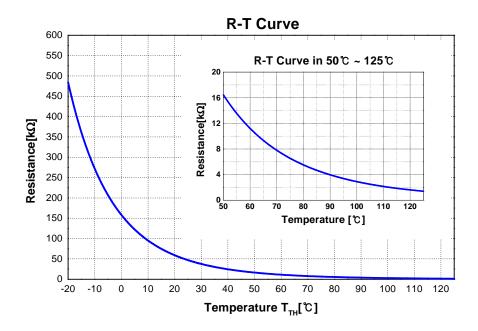
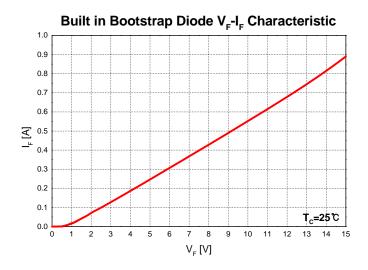


Figure. 6. R-T Curve of The Built-in Thermistor

### **Bootstrap Diode Part**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 0.1 A, T <sub>C</sub> = 25°C	-	2.5	-	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 0.1 A, T <sub>C</sub> = 25°C	-	80	_	ns



#### Note:

6. Built in bootstrap diode includes around 15  $\,\Omega$  resistance characteristic.

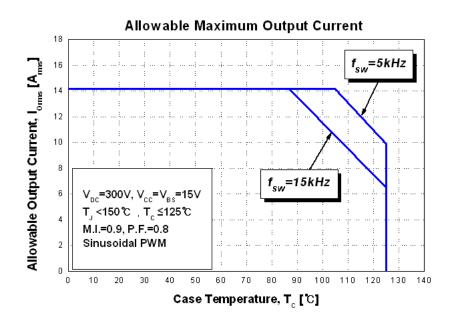
Figure 7. Built in Bootstrap Diode Characteristic

## **Recommended Operating Conditions**

Cumbal	Doromotor	Conditions	Value			I In:4
Symbol	Parameter	eter Conditions -		Тур.	Max.	Unit
V <sub>PN</sub>	Supply Voltage	Applied between P - N <sub>U</sub> , N <sub>V</sub> , N <sub>W</sub>	-	300	400	V
V <sub>CC</sub>	Control Supply Voltage	Applied between V <sub>CC(H)</sub> , V <sub>CC(L)</sub> - COM	13.5	15	16.5	V
$V_{BS}$	High - Side Bias Voltage	Applied between $V_{B(U)}$ - $V_{S(U)}$ , $V_{B(V)}$ - $V_{S(V)}$ , $V_{B(W)}$ - $V_{S(W)}$	13.0	15	18.5	V
$dV_{CC}$ / $dt$ , $dV_{BS}$ / $dt$	Control Supply Variation		- 1	-	1	V / μs
t <sub>dead</sub>	Blanking Time for Preventing Arm - Short	For each input signal	1.5	-	-	μS
f <sub>PWM</sub>	PWM Input Signal	- 40°C < T <sub>J</sub> < 150°C	-	-	20	kHz
V <sub>SEN</sub>	Voltage for Current Sensing	Applied between N <sub>U</sub> , N <sub>V</sub> , N <sub>W</sub> - COM (Including surge voltage)	- 4		4	V
P <sub>WIN(ON)</sub>	Minimun Input Pulse	(Note 7)	0.7	-	-	μS
P <sub>WIN(OFF)</sub>	Width		0.7	-	-	

#### Note:

7. This product might not make response if input pulse width is less than the recommanded value.



#### Note:

8. This allowable output current value is the reference data for the safe operation of this product. This may be different from the actual application and operating condition.

Figure 8. Allowable Maximum Output Current

## **Mechanical Characteristics and Ratings**

Parameter	Co		Unit			
raiailletei		Min.	Тур.	Max.	Oiiit	
Device Flatness	Note Figure 9	Note Figure 9		-	+ 120	μm
Mounting Torque	Mounting Screw: - M3	Recommended 0.7 N • m	0.6	0.7	0.8	N • m
	Note Figure 10	Recommended 7.1 kg • cm	6.2	7.1	8.1	kg • cm
Weight			-	11	-	g

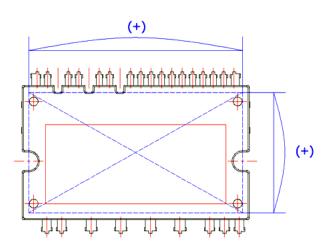


Figure 9. Flatness Measurement Position

Pre - Screwing : 1→2
Final Screwing : 2→1

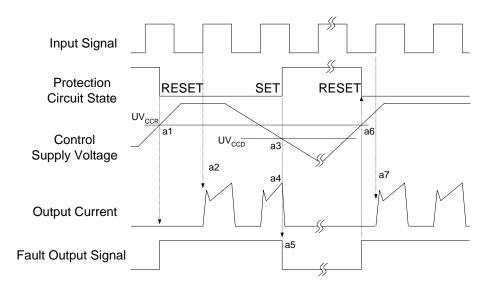
#### Note:

9. Do not make over torque when mounting screws. Much mounting torque may cause ceramic cracks, as well as bolts and Al heat - sink destruction.

10. Avoid one side tightening stress. Figure 10 shows the recommended torque order for mounting screws. Uneven mounting can cause the ceramic substrate of the Motion SPM® 45 product to be damaged. The Pre - Screwing torque is set to 20 ~ 30% of maximum torque rating.

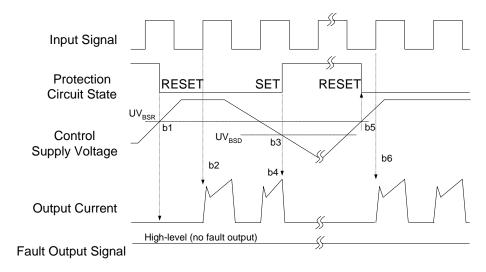
Figure 10. Mounting Screws Torque Order

### **Time Charts of Protective Function**



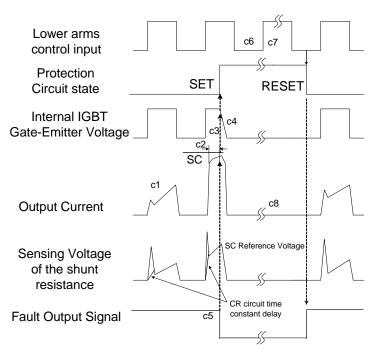
- a1 : Control supply voltage rises: After the voltage rises  $UV_{CCR}$ , the circuits start to operate when next input is applied.
- a2: Normal operation: IGBT ON and carrying current.
- a3 : Under voltage detection (UV<sub>CCD</sub>).
- a4: IGBT OFF in spite of control input condition.
- a5 : Fault output operation starts.
- a6 : Under voltage reset (UV $_{CCR}$ ).
- a7: Normal operation: IGBT ON and carrying current.

Figure 11. Under - Voltage Protection (Low - Side)



- b1 : Control supply voltage rises: After the voltage reaches UV<sub>BSR</sub>, the circuits start to operate when next input is applied.
- b2: Normal operation: IGBT ON and carrying current.
- b3 : Under voltage detection (UV<sub>BSD</sub>).
- b4: IGBT OFF in spite of control input condition, but there is no fault output signal.
- b5 : Under voltage reset (UV<sub>BSR</sub>)
- b6: Normal operation: IGBT ON and carrying current

Figure 12. Under - Voltage Protection (High - Side)

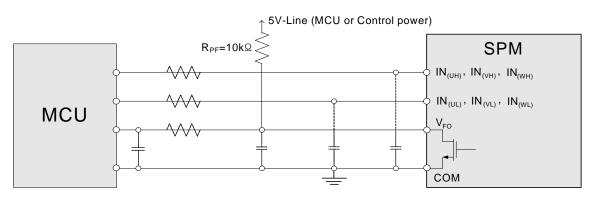


(with the external shunt resistance and CR connection)

- c1: Normal operation: IGBT ON and carrying current.
- c2 : Short circuit current detection (SC trigger).
- c3: Hard IGBT gate interrupt.
- c4: IGBT turns OFF.
- c5 : Input "L" : IGBT OFF state.
- c6 : Input "H": IGBT ON state, but during the active period of fault output the IGBT doesn't turn ON.
- c7: IGBT OFF state

Figure 13. Short - Circuit Current Protection (Low - Side Operation only)

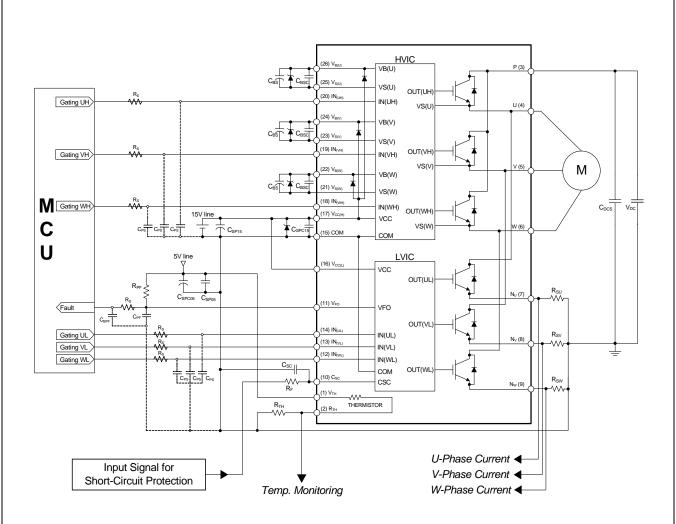
## **Input/Output Interface Circuit**



#### Note

Figure 14. Recommended CPU I/O Interface Circuit

<sup>1)</sup> RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The input signal section of the Motion SPM<sup>®</sup> 45 product integrates 5 kΩ (typ.) pull - down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at input terminal.

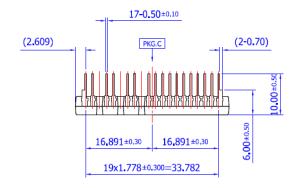


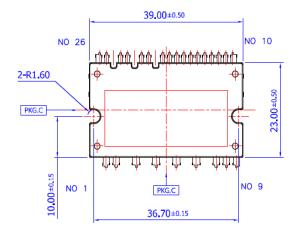
#### Note:

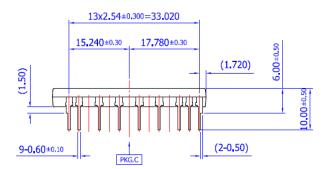
- 1) To avoid malfunction, the wiring of each input should be as short as possible. (less than 2 3 cm)
- 2) By virtue of integrating an application specific type HVIC inside the Motion SPM<sup>®</sup> 45 product, direct coupling to CPU terminals without any opto coupler or transformer isolation is possible.
- 3) V<sub>FO</sub> output is open drain type. This signal line should be pulled up to the positive side of the MCU or control power supply with a resistor that makes I<sub>FO</sub> up to 1 mA. Please refer to Figure 14.
- 4)  $C_{SP15}$  of around 7 times larger than bootstrap capacitor  $C_{BS}$  is recommended.
- 5) Input signal is High Active type. There is a 5 k $\Omega$  resistor inside the IC to pull down each input signal line to GND. RC coupling circuits is recommanded for the prevention of input signal oscillation. R<sub>S</sub>C<sub>PS</sub> time constant should be selected in the range 50 ~ 150 ns. (Recommended R<sub>S</sub> = 100  $\Omega$ , C<sub>PS</sub> = 1 nF)
- 6) To prevent errors of the protection function, the wiring around  $R_F$  and  $C_{SC}$  should be as short as possible.
- 7) In the short circuit protection circuit, please select the  $R_FC_{SC}$  time constant in the range 1.5 ~ 2  $\mu s$ .
- 8) The connection between control GND line and power GND line which includes the N<sub>U</sub>, N<sub>V</sub>, N<sub>W</sub> must be connected to only one point. Please do not connect the control GND to the power GND by the broad pattern. Also, the wiring distance between control GND and power GND should be as short as possible.
- 9) Each capacitor should be mounted as close to the pins of the SPM as possible.
- 10) To prevent surge destruction, the wiring between the smoothing capacitor and the P & GND pins should be as short as possible. The use of a high frequency non inductive capacitor of around 0.1 ~ 0.22 µF between the P & GND pins is recommended.
- 11) Relays are used at almost every systems of electrical equipments of home appliances. In these cases, there should be sufficient distance between the CPU and the relays.
- 12) The zener diode or transient voltage suppressor should be adopted for the protection of ICs from the surge destruction between each pair of control supply terminals. (Recommanded zener diode is 22V/1W, which has the lower zener impedance characteristic than about 15\Omega)
- 13) Please choose the electrolytic capacitor with good temperature characteristic in  $C_{BS}$ . Also, choose 0.1 ~ 0.2  $\mu F$  R category ceramic capacitors with good temperature and frequency characteristics in  $C_{BSC}$ .
- 14) For the detailed information, please refer to the AN 9070, AN 9071, AN 9072, RD 344, and RD 345.

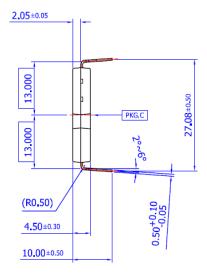
Figure 15. Typical Application Circuit

## **Detailed Package Outline Drawings (FNC42060F)**

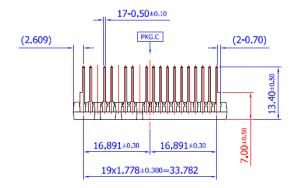


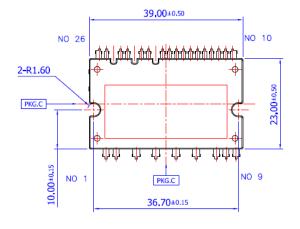


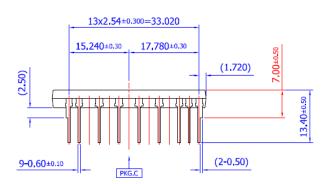


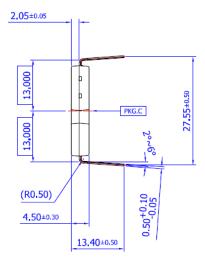


## **Detailed Package Outline Drawings (FNC42060F2, Long Terminal Type)**













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